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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	6144
Total RAM Bits	36864
Number of I/O	97
Number of Gates	250000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agl250v5-fgg144i

Table 2-33 • Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case V_{CCI} (per standard) Applicable to Standard I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option ¹ (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	8 mA	8	High	5	–	0.97	1.85	0.18	0.83	0.66	1.89	1.46	1.96	2.26	ns
3.3 V LVCMOS Wide Range ²	100 μA	8	High	5	–	0.97	2.62	0.18	1.17	0.66	2.63	2.02	2.79	3.17	ns
2.5 V LVCMOS	8 mA	8	High	5	–	0.97	1.88	0.18	1.04	0.66	1.92	1.63	1.95	2.15	ns
1.8 V LVCMOS	4 mA	4	High	5	–	0.97	2.18	0.18	0.98	0.66	2.22	1.93	1.97	2.06	ns
1.5 V LVCMOS	2 mA	2	High	5	–	0.97	2.51	0.18	1.14	0.66	2.56	2.21	1.99	2.03	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Single-Ended I/O Characteristics

3.3 V LVTTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic (LVTTTL) is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTTL input buffer and push-pull output buffer. Furthermore, all LVCMOS 3.3 V software macros comply with LVCMOS 3.3 V wide range as specified in the JESD8a specification.

Table 2-47 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

3.3 V LVTTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.8	2	3.6	0.4	2.4	2	2	25	27	10	10
4 mA	−0.3	0.8	2	3.6	0.4	2.4	4	4	25	27	10	10
6 mA	−0.3	0.8	2	3.6	0.4	2.4	6	6	51	54	10	10
8 mA	−0.3	0.8	2	3.6	0.4	2.4	8	8	51	54	10	10
12 mA	−0.3	0.8	2	3.6	0.4	2.4	12	12	103	109	10	10
16 mA	−0.3	0.8	2	3.6	0.4	2.4	16	16	132	127	10	10
24 mA	−0.3	0.8	2	3.6	0.4	2.4	24	24	268	181	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-48 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

3.3 V LVTTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.8	2	3.6	0.4	2.4	2	2	25	27	10	10
4 mA	−0.3	0.8	2	3.6	0.4	2.4	4	4	25	27	10	10
6 mA	−0.3	0.8	2	3.6	0.4	2.4	6	6	51	54	10	10
8 mA	−0.3	0.8	2	3.6	0.4	2.4	8	8	51	54	10	10
12 mA	−0.3	0.8	2	3.6	0.4	2.4	12	12	103	109	10	10
16 mA	−0.3	0.8	2	3.6	0.4	2.4	16	16	103	109	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

3.3 V LVC MOS Wide Range

Table 2-63 • Minimum and Maximum DC Input and Output Levels for LVC MOS 3.3 V Wide Range
Applicable to Advanced I/O Banks

3.3 V LVC MOS Wide Range		VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ²	IIH ³
Drive Strength	Equivalent Software Default Drive Strength Option ¹	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	μA	μA	Max. mA ⁴	Max. mA ⁴	μA^5	μA^5
100 μA	2 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	25	27	10	10
100 μA	4 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	25	27	10	10
100 μA	6 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	51	54	10	10
100 μA	8 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	51	54	10	10
100 μA	12 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	103	109	10	10
100 μA	16 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	132	127	10	10
100 μA	24 mA	−0.3	0.8	2	3.6	0.2	VDD − 0.2	100	100	268	181	10	10

Notes:

1. The minimum drive strength for any LVC MOS 3.3 V software configuration when run in wide range is $\pm 100 \mu\text{A}$. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3 \text{ V} < V_{\text{IN}} < V_{\text{IL}}$.
3. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{\text{IH}} < V_{\text{IN}} < V_{\text{CCI}}$. Input current is larger when operating outside recommended ranges
4. Currents are measured at 100°C junction temperature and maximum voltage.
5. Currents are measured at 85°C junction temperature.
6. Software default selection highlighted in gray.

Table 2-75 • 3.3 V LVC MOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_j = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$, Worst-Case $V_{CCI} = 2.7$
Applicable to Standard Plus Banks

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 μA	2 mA	Std.	1.55	6.69	0.26	1.32	1.10	6.69	5.73	3.41	3.72	12.48	11.52	ns
100 μA	4 mA	Std.	1.55	6.69	0.26	1.32	1.10	6.69	5.73	3.41	3.72	12.48	11.52	ns
100 μA	6 mA	Std.	1.55	5.58	0.26	1.32	1.10	5.58	5.01	3.77	4.35	11.36	10.79	ns
100 μA	8 mA	Std.	1.55	5.58	0.26	1.32	1.10	5.58	5.01	3.77	4.35	11.36	10.79	ns
100 μA	12 mA	Std.	1.55	4.82	0.26	1.32	1.10	4.82	4.44	4.02	4.76	10.61	10.23	ns
100 μA	16 mA	Std.	1.55	4.82	0.26	1.32	1.10	4.82	4.44	4.02	4.76	10.61	10.23	ns

Notes:

1. The minimum drive strength for any LVC MOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-76 • 3.3 V LVC MOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_j = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$, Worst-Case $V_{CCI} = 2.7$
Applicable to Standard Plus Banks

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 μA	2 mA	Std.	1.55	4.10	0.26	1.32	1.10	4.10	3.30	3.40	3.92	9.89	9.09	ns
100 μA	4 mA	Std.	1.55	4.10	0.26	1.32	1.10	4.10	3.30	3.40	3.92	9.89	9.09	ns
100 μA	6 mA	Std.	1.55	3.51	0.26	1.32	1.10	3.51	2.79	3.76	4.56	9.30	8.57	ns
100 μA	8 mA	Std.	1.55	3.51	0.26	1.32	1.10	3.51	2.79	3.76	4.56	9.30	8.57	ns
100 μA	12 mA	Std.	1.55	3.20	0.26	1.32	1.10	3.20	2.52	4.01	4.97	8.99	8.31	ns
100 μA	16 mA	Std.	1.55	3.20	0.26	1.32	1.10	3.20	2.52	4.01	4.97	8.99	8.31	ns

Notes:

1. The minimum drive strength for any LVC MOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.
3. Software default selection highlighted in gray.

1.2 V LVCMOS (JESD8-12A)

Low-Voltage CMOS for 1.2 V complies with the LVCMOS standard JESD8-12A for general purpose 1.2 V applications. It uses a 1.2 V input buffer and a push-pull output buffer. Furthermore, all LVCMOS 1.2 V software macros comply with LVCMOS 1.2 V wide range as specified in the JESD8-12A specification.

Table 2-127 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

1.2 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	2	2	20	26	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-128 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

1.2 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	2	2	20	26	10	10

Notes:

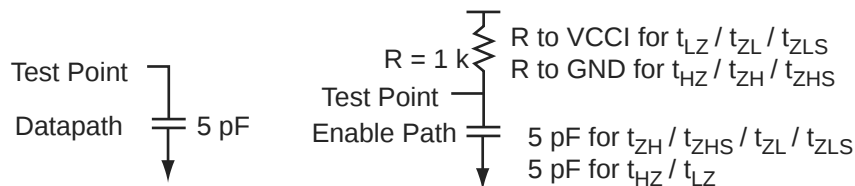
1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-129 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard I/O Banks

1.2 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
1 mA	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	1	1	20	26	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

**Figure 2-11 • AC Loading****Table 2-130 • AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	1.2	0.6	5

Note: *Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.

Timing Characteristics

1.2 V DC Core Voltage

Table 2-131 • 1.2 V LVCMOS Low Slew

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	8.37	0.26	1.60	1.10	8.04	7.17	3.94	3.52	13.82	12.95	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-132 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	3.60	0.26	1.60	1.10	3.47	3.36	3.93	3.65	9.26	9.14	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-133 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	7.59	0.26	1.59	1.10	7.29	6.54	3.30	3.35	13.08	12.33	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-134 • 1.2 V LVCMOS High Slew

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
2 mA	Std.	1.55	3.22	0.26	1.59	1.10	3.11	2.78	3.29	3.48	8.90	8.57	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Input Register

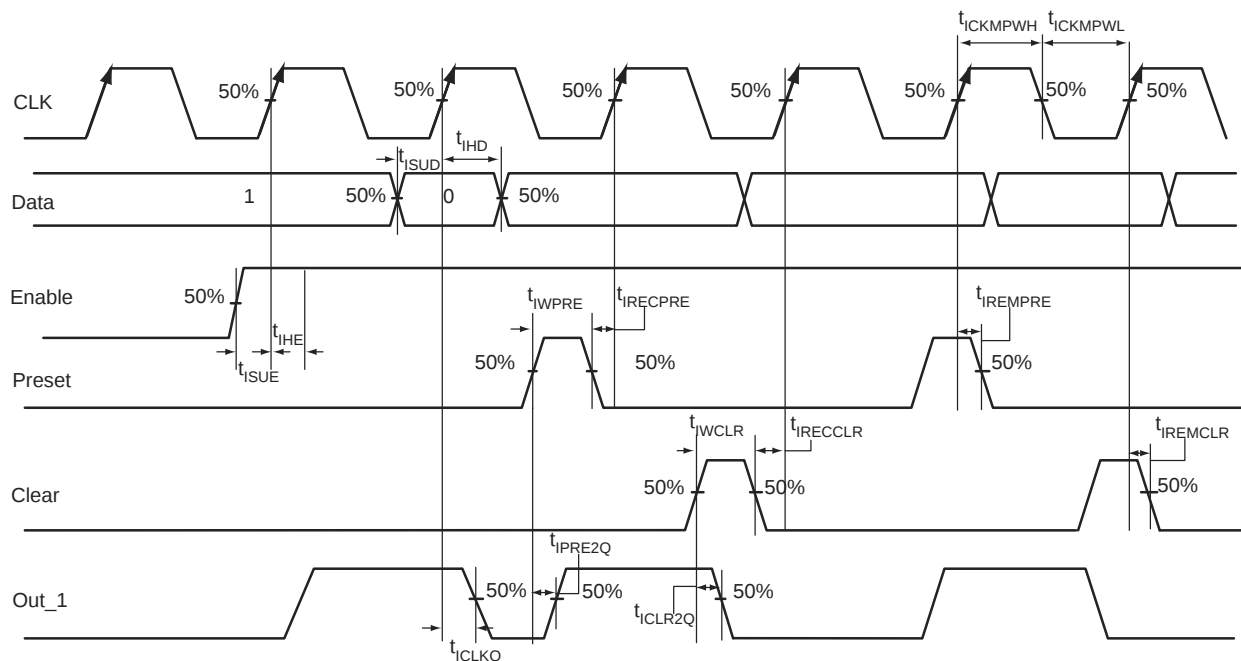


Figure 2-18 • Input Register Timing Diagram

Timing Characteristics

1.5 V DC Core Voltage

Table 2-157 • Input Data Register Propagation Delays

Commercial-Case Conditions: $T_j = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.42	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.47	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	ns
t_{ISUE}	Enable Setup Time for the Input Data Register	0.67	ns
t_{IHE}	Enable Hold Time for the Input Data Register	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.79	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.79	ns
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	0.00	ns
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	0.24	ns
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	0.00	ns
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	0.24	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.19	ns
t_{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.19	ns
$t_{ICKMPWH}$	Clock Minimum Pulse Width High for the Input Data Register	0.31	ns
$t_{ICKMPWL}$	Clock Minimum Pulse Width Low for the Input Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

1.2 V DC Core Voltage**Table 2-162 • Output Enable Register Propagation Delays****Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$**

Parameter	Description	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	1.10	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	1.15	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	ns
t_{OESUE}	Enable Setup Time for the Output Enable Register	1.22	ns
t_{OEHE}	Enable Hold Time for the Output Enable Register	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	1.65	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	1.65	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.24	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.24	ns
$t_{OEWCCLR}$	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OEWPRES}$	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.31	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

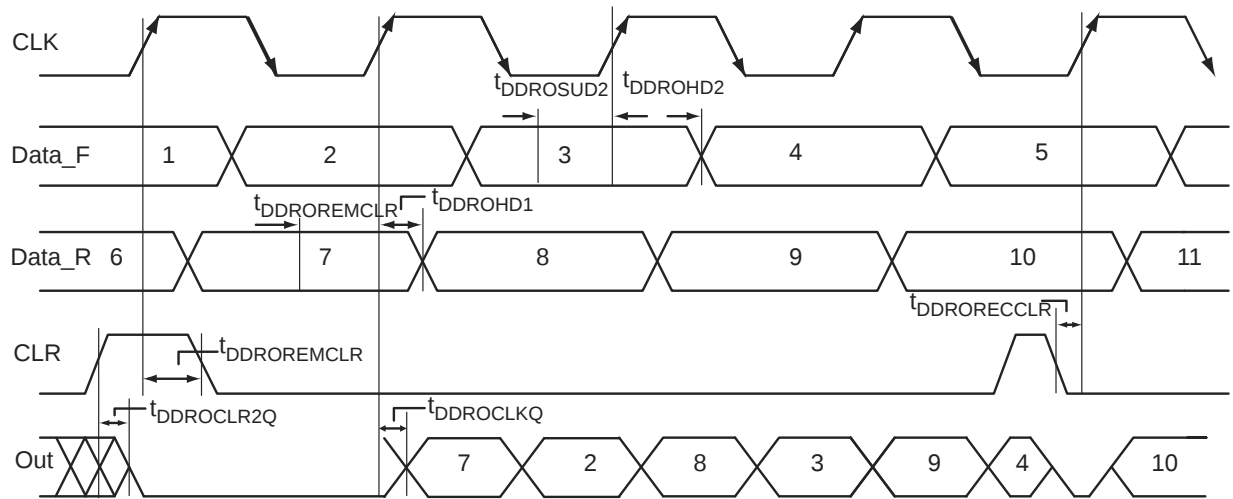


Figure 2-24 • Output DDR Timing Diagram

Timing Characteristics

1.5 V DC Core Voltage

Table 2-167 • Output DDR Propagation Delays
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{DDROCLKQ}	Clock-to-Out of DDR for Output DDR	1.07	ns
t_{DDROSUD1}	Data_F Data Setup for Output DDR	0.67	ns
t_{DDROSUD2}	Data_R Data Setup for Output DDR	0.67	ns
t_{DDROHD1}	Data_F Data Hold for Output DDR	0.00	ns
t_{DDROHD2}	Data_R Data Hold for Output DDR	0.00	ns
$t_{\text{DDROCLR2Q}}$	Asynchronous Clear-to-Out for Output DDR	1.38	ns
$t_{\text{DDROEMCLR}}$	Asynchronous Clear Removal Time for Output DDR	0.00	ns
$t_{\text{DDROECCLR}}$	Asynchronous Clear Recovery Time for Output DDR	0.23	ns
$t_{\text{DDROWCLR1}}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.19	ns
$t_{\text{DDROCKMPWH}}$	Clock Minimum Pulse Width High for the Output DDR	0.31	ns
$t_{\text{DDROCKMPWL}}$	Clock Minimum Pulse Width Low for the Output DDR	0.28	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	250.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

VersaTile Characteristics

VersaTile Specifications as a Combinatorial Module

The IGLOO library offers all combinations of LUT-3 combinatorial functions. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the *IGLOO, Fusion, and ProASIC3 Macro Library Guide*.

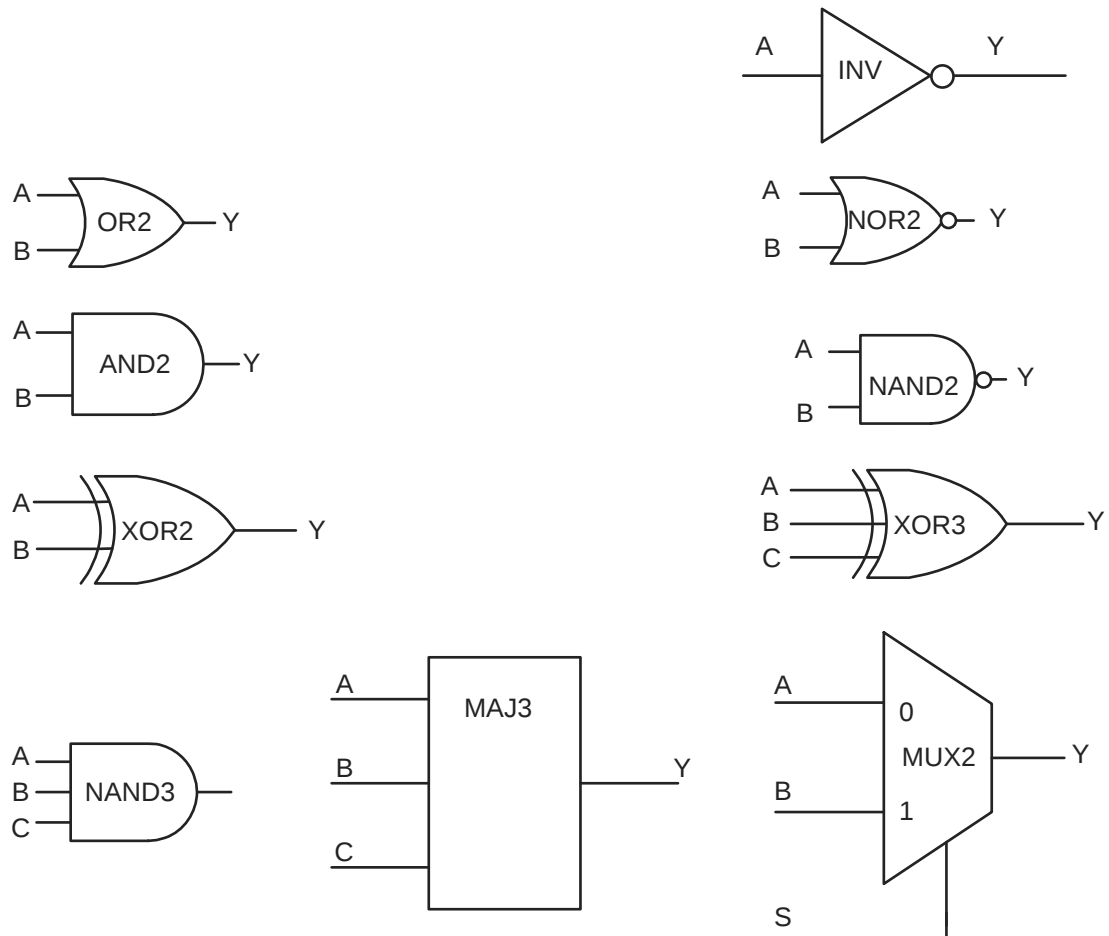


Figure 2-25 • Sample of Combinatorial Cells

Table 2-185 • AGL250 Global Resource**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.14\text{ V}$**

Parameter	Description	Std.		Units
		Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	2.11	2.57	ns
t_{RCKH}	Input High Delay for Global Clock	2.19	2.81	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.62	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-186 • AGL400 Global Resource**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.14\text{ V}$**

Parameter	Description	Std.		Units
		Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	2.18	2.64	ns
t_{RCKH}	Input High Delay for Global Clock	2.27	2.89	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.62	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Timing Characteristics

1.5 V DC Core Voltage

Table 2-191 • RAM4K9

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{AS}	Address setup time	0.83	ns
t_{AH}	Address hold time	0.16	ns
t_{ENS}	REN, WEN setup time	0.81	ns
t_{ENH}	REN, WEN hold time	0.16	ns
t_{BKS}	BLK setup time	1.65	ns
t_{BKH}	BLK hold time	0.16	ns
t_{DS}	Input data (DIN) setup time	0.71	ns
t_{DH}	Input data (DIN) hold time	0.36	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	3.53	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	3.06	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	1.81	ns
t_{C2CWWL}^1	Address collision clk-to-clk delay for reliable write after write on same address – Applicable to Closing Edge	0.23	ns
t_{C2CRWL}^1	Address collision clk-to-clk delay for reliable read access after write on same address – Applicable to Opening Edge	0.35	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address – Applicable to Opening Edge	0.41	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	2.06	ns
	RESET Low to data out Low on DOUT (pipelined)	2.06	ns
$t_{REMRSTB}$	RESET removal	0.61	ns
$t_{RECRSTB}$	RESET recovery	3.21	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.68	ns
t_{CYC}	Clock cycle time	6.24	ns
F_{MAX}	Maximum frequency	160	MHz

Notes:

1. For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

CS121	
Pin Number	AGL060 Function
K10	VPUMP
K11	GDB1/IO47RSB0
L1	VMV1
L2	GNDQ
L3	IO65RSB1
L4	IO63RSB1
L5	IO61RSB1
L6	IO58RSB1
L7	IO57RSB1
L8	IO55RSB1
L9	GNDQ
L10	GDA0/IO50RSB0
L11	VMV1

QN132	
Pin Number	AGL060 Function
C16	IO60RSB1
C17	IO57RSB1
C18	NC
C19	TCK
C20	VMV1
C21	VPUMP
C22	VJTAG
C23	VCCIB0
C24	NC
C25	NC
C26	GCA1/IO42RSB0
C27	GCC0/IO39RSB0
C28	VCCIB0
C29	IO29RSB0
C30	GNDQ
C31	GBA1/IO27RSB0
C32	GBB0/IO24RSB0
C33	VCC
C34	IO19RSB0
C35	IO16RSB0
C36	IO13RSB0
C37	GAC1/IO10RSB0
C38	NC
C39	GAA0/IO05RSB0
C40	VMV0
D1	GND
D2	GND
D3	GND
D4	GND

FG256	
Pin Number	AGL400 Function
H3	GFB1/IO146PPB3
H4	VCOMPLF
H5	GFC0/IO147NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO67NPB1
H13	GCB1/IO68PPB1
H14	GCA0/IO69NPB1
H15	NC
H16	GCB0/IO68NPB1
J1	GFA2/IO144PPB3
J2	GFA1/IO145PDB3
J3	VCCPLF
J4	IO143NDB3
J5	GFB2/IO143PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO71PPB1
J13	GCA1/IO69PPB1
J14	GCC2/IO72PPB1
J15	NC
J16	GCA2/IO70PDB1
K1	GFC2/IO142PDB3
K2	IO144NPB3
K3	IO141PPB3
K4	IO120RSB2
K5	VCCIB3
K6	VCC
K7	GND
K8	GND

FG256	
Pin Number	AGL400 Function
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO71NPB1
K14	IO74RSB1
K15	IO72NPB1
K16	IO70NDB1
L1	IO142NDB3
L2	IO141NPB3
L3	IO125RSB2
L4	IO139RSB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO78VPB1
L14	IO76VDB1
L15	IO76UDB1
L16	IO75PDB1
M1	IO140PDB3
M2	IO130RSB2
M3	IO138NPB3
M4	GEC0/IO137NPB3
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	IO108RSB2
M9	IO101RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	IO83RSB2
M14	GDB1/IO78UPB1

FG256	
Pin Number	AGL400 Function
M15	GDC1/IO77UDB1
M16	IO75NDB1
N1	IO140NDB3
N2	IO138PPB3
N3	GEC1/IO137PPB3
N4	IO131RSB2
N5	GNDQ
N6	GEA2/IO134RSB2
N7	IO117RSB2
N8	IO111RSB2
N9	IO99RSB2
N10	IO94RSB2
N11	IO87RSB2
N12	GNDQ
N13	IO93RSB2
N14	VJTAG
N15	GDC0/IO77VDB1
N16	GDA1/IO79UDB1
P1	GEB1/IO136PDB3
P2	GEB0/IO136NDB3
P3	VMV2
P4	IO129RSB2
P5	IO128RSB2
P6	IO122RSB2
P7	IO115RSB2
P8	IO110RSB2
P9	IO98RSB2
P10	IO95RSB2
P11	IO88RSB2
P12	IO84RSB2
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO79VDB1
R1	GEA1/IO135PDB3
R2	GEA0/IO135NDB3
R3	IO127RSB2
R4	GEC2/IO132RSB2

FG484	
Pin Number	AGL400 Function
G5	IO151UDB3
G6	GAC2/IO153UDB3
G7	IO06RSB0
G8	GNDQ
G9	IO10RSB0
G10	IO19RSB0
G11	IO26RSB0
G12	IO30RSB0
G13	IO40RSB0
G14	IO46RSB0
G15	GNDQ
G16	IO47RSB0
G17	GBB2/IO61PPB1
G18	IO53RSB0
G19	IO63NDB1
G20	NC
G21	NC
G22	NC
H1	NC
H2	NC
H3	VCC
H4	IO150PDB3
H5	IO08RSB0
H6	IO153VDB3
H7	IO152VDB3
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO25RSB0
H12	IO31RSB0
H13	VCCIB0
H14	VCCIB0
H15	VMV1
H16	GBC2/IO62PDB1
H17	IO65RSB1
H18	IO52RSB0

FG484	
Pin Number	AGL400 Function
U1	NC
U2	NC
U3	NC
U4	GEB1/IO136PDB3
U5	GEB0/IO136NDB3
U6	VMV2
U7	IO129RSB2
U8	IO128RSB2
U9	IO122RSB2
U10	IO115RSB2
U11	IO110RSB2
U12	IO98RSB2
U13	IO95RSB2
U14	IO88RSB2
U15	IO84RSB2
U16	TCK
U17	VPUMP
U18	TRST
U19	GDA0/IO79VDB1
U20	NC
U21	NC
U22	NC
V1	NC
V2	NC
V3	GND
V4	GEA1/IO135PDB3
V5	GEA0/IO135NDB3
V6	IO127RSB2
V7	GEC2/IO132RSB2
V8	IO123RSB2
V9	IO118RSB2
V10	IO112RSB2
V11	IO106RSB2
V12	IO100RSB2
V13	IO96RSB2
V14	IO89RSB2

FG484	
Pin Number	AGL400 Function
V15	IO85RSB2
V16	GDB2/IO81RSB2
V17	TDI
V18	NC
V19	TDO
V20	GND
V21	NC
V22	NC
W1	NC
W2	NC
W3	NC
W4	GND
W5	IO126RSB2
W6	FF/GEB2/IO133RSB2
W7	IO124RSB2
W8	IO116RSB2
W9	IO113RSB2
W10	IO107RSB2
W11	IO105RSB2
W12	IO102RSB2
W13	IO97RSB2
W14	IO92RSB2
W15	GDC2/IO82RSB2
W16	IO86RSB2
W17	GDA2/IO80RSB2
W18	TMS
W19	GND
W20	NC
W21	NC
W22	NC
Y1	VCCIB3
Y2	NC
Y3	NC
Y4	NC
Y5	GND
Y6	NC

FG484	
Pin Number	AGL1000 Function
K11	GND
K12	GND
K13	GND
K14	VCC
K15	VCCIB1
K16	GCC1/IO91PPB1
K17	IO90NPB1
K18	IO88PDB1
K19	IO88NDB1
K20	IO94NPB1
K21	IO98NDB1
K22	IO98PDB1
L1	NC
L2	IO200PDB3
L3	IO210NPB3
L4	GFB0/IO208NPB3
L5	GFA0/IO207NDB3
L6	GFB1/IO208PPB3
L7	VCOMPLF
L8	GFC0/IO209NPB3
L9	VCC
L10	GND
L11	GND
L12	GND
L13	GND
L14	VCC
L15	GCC0/IO91NPB1
L16	GCB1/IO92PPB1
L17	GCA0/IO93NPB1
L18	IO96NPB1
L19	GCB0/IO92NPB1
L20	IO97PDB1
L21	IO97NDB1
L22	IO99NPB1
M1	NC
M2	IO200NDB3

Revision / Version	Changes	Page
DC & Switching, cont'd.	Table 2-49 • Minimum and Maximum DC Input and Output Levels for LVCMOS 3.3 V Wide Range is new.	2-39
Revision 9 (Jul 2008) Product Brief v1.1 DC and Switching Characteristics Advance v0.3	As a result of the Libero IDE v8.4 release, Actel now offers a wide range of core voltage support. The document was updated to change 1.2 V / 1.5 V to 1.2 V to 1.5 V.	N/A
Revision 8 (Jun 2008) DC and Switching Characteristics Advance v0.2	As a result of the Libero IDE v8.4 release, Actel now offers a wide range of core voltage support. The document was updated to change 1.2 V / 1.5 V to 1.2 V to 1.5 V.	N/A
	Tables have been updated to reflect default values in the software. The default I/O capacitance is 5 pF. Tables have been updated to include the LVCMOS 1.2 V I/O set. DDR Tables have two additional data points added to reflect both edges for Input DDR setup and hold time. The power data table has been updated to match SmartPower data rather than simulation values. AGL015 global clock delays have been added.	N/A
	Table 2-1 • Absolute Maximum Ratings was updated to combine the VCCI and VMV parameters in one row. The word "output" from the parameter description for VCCI and VMV, and table note 3 was added.	2-1
	Table 2-2 • Recommended Operating Conditions 1 was updated to add references to tables notes 4, 6, 7, and 8. VMV was added to the VCCI parameter row, and table note 9 was added.	2-2
	In Table 2-3 • Flash Programming Limits – Retention, Storage, and Operating Temperature ¹ , the maximum operating junction temperature was changed from 110° to 100°.	2-3
	VMV was removed from Table 2-4 • Overshoot and Undershoot Limits 1. The table title was modified to remove "as measured on quiet I/Os." Table note 2 was revised to remove "estimated SSO density over cycles." Table note 3 was revised to remove "refers only to overshoot/undershoot limits for simultaneous switching I/Os."	2-3
	The "PLL Behavior at Brownout Condition" section is new.	2-4
	Figure 2-2 • V2 Devices – I/O State as a Function of VCCI and VCC Voltage Levels is new.	2-5
	EQ 2 was updated. The temperature was changed to 100°C, and therefore the end result changed.	2-6
	The table notes for Table 2-9 • Quiescent Supply Current (IDD) Characteristics, IGLOO Flash*Freeze Mode*, Table 2-10 • Quiescent Supply Current (IDD) Characteristics, IGLOO Sleep Mode*, and Table 2-11 • Quiescent Supply Current (IDD) Characteristics, IGLOO Shutdown Mode were updated to remove VMV and include PDC6 and PDC7. VCCI and VJTAG were removed from the statement about IDD in the table note for Table 2-11 • Quiescent Supply Current (IDD) Characteristics, IGLOO Shutdown Mode.	2-7
	Note 2 of Table 2-12 • Quiescent Supply Current (IDD), No IGLOO Flash*Freeze Mode ¹ was updated to include VCCPLL. Note 4 was updated to include PDC6 and PDC7.	2-9